



Design of an Ultra-High Efficiency GaN High-Power Amplifier for SAR Remote Sensing

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SweepSAR Technique

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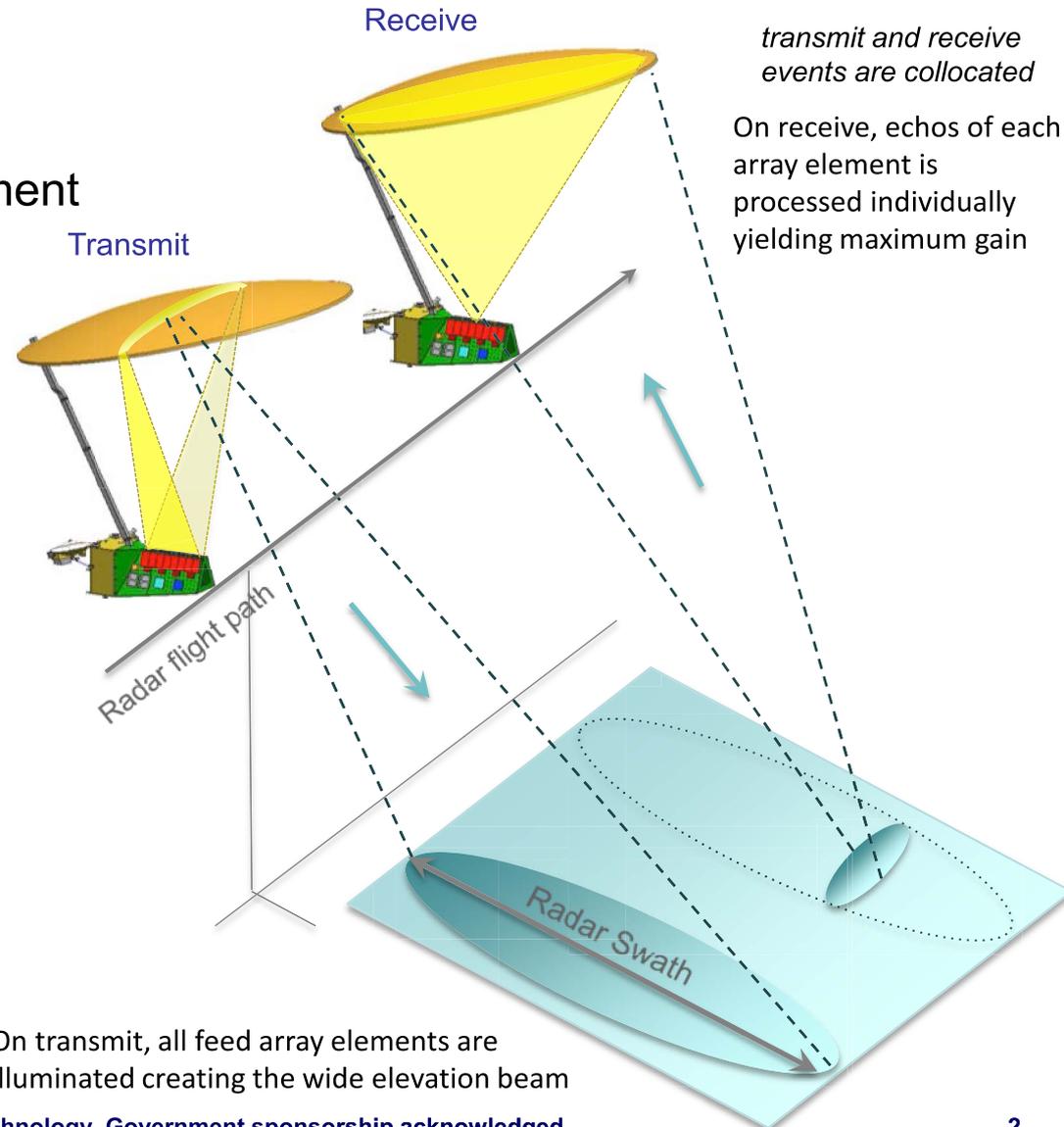
- increased swath and resolution
- TRM drives single feed array element
- digitally rcvrs + on-board cal → on-orbit beamforming

Challenges:

- high rx duty cycle (near 100%)
- shorter, high peak power transmit pulse to achieve SNR

SweepSAR requires high-power and high efficiency PAs

GaN is a key enabling technology

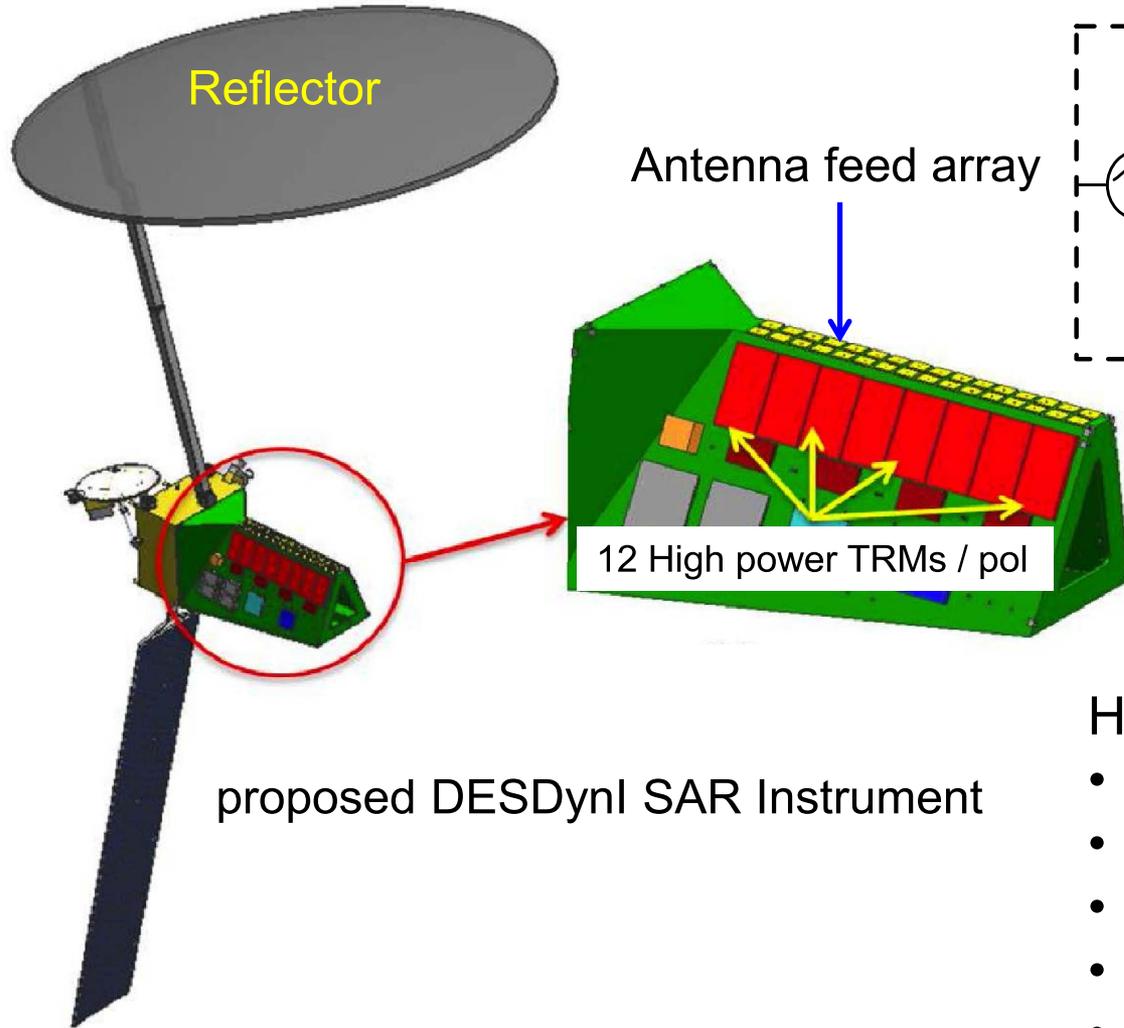


On transmit, all feed array elements are illuminated creating the wide elevation beam

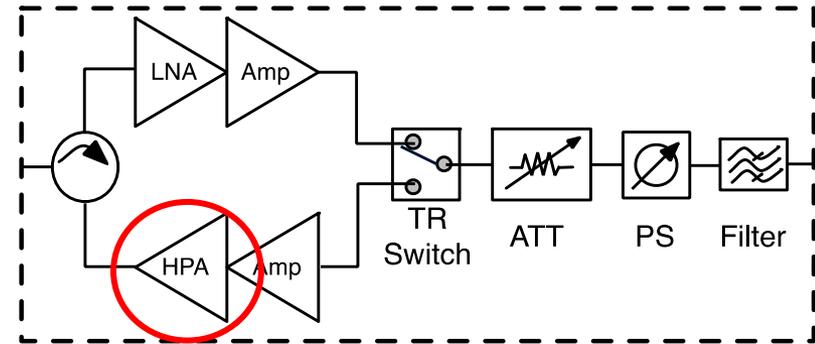


Proposed DESDynI SAR instrument

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proposed DESDynI SAR Instrument



Notional TRM Block diagram

HPA requirements:

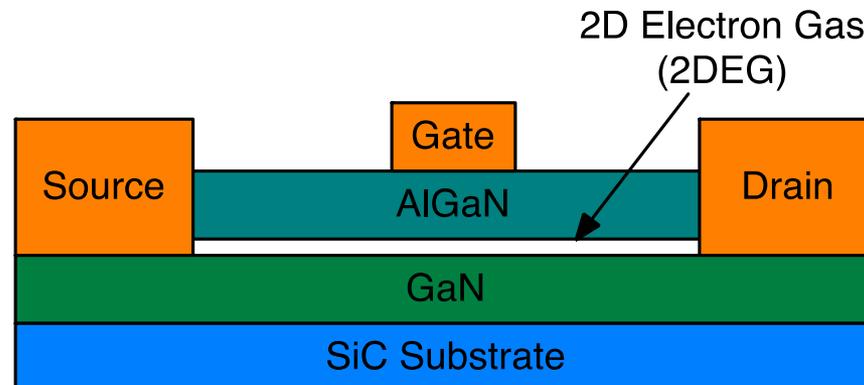
- > 100 W
- > 60 % efficiency
- compact
- passive thermal management
- reliable



GaN HEMT Technology

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- Wide bandgap material
 - high breakdown (10 X GaAs)
 - high power density (5 X GaAs)
- Bandgap engineering with AlGaN / GaN layers
- SiC substrate – low thermal resistance
- Low parasitic capacitance – high efficiency amplifier modes
- Advanced GaN HEMTs
 - field plate to control electric field on gate





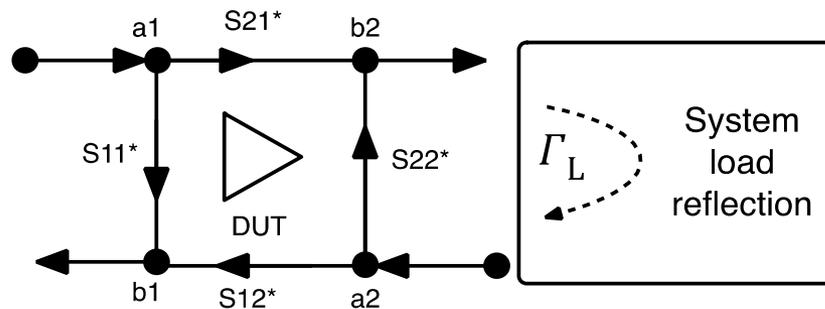
Large Signal Characterization

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- **Load-pull characterize non-linear device response**
 - presents impedances to the DUT at fundamental and harmonics
- **In large signal, linear approximation not valid**

$$I_{DS}(V_{GS}) \simeq i_{DS}(V_{GS}) + \underline{a_1 v_{gs}} + \underline{a_2 v_{gs}^2} + \underline{a_3 v_{gs}^3} + \dots$$

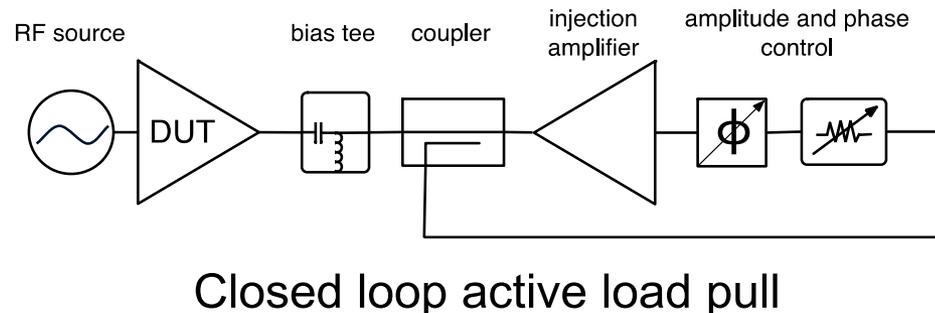
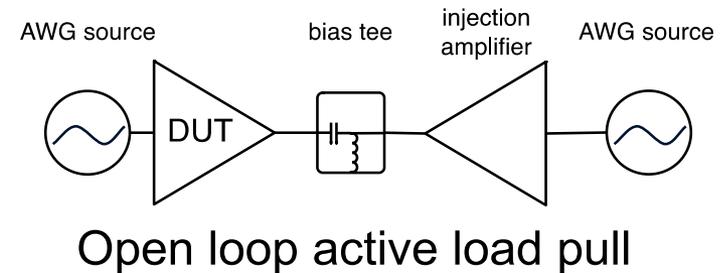
- Performance is non-linear (cannot use s-parameters) and depends on impedance presented to device





Load-pull Techniques

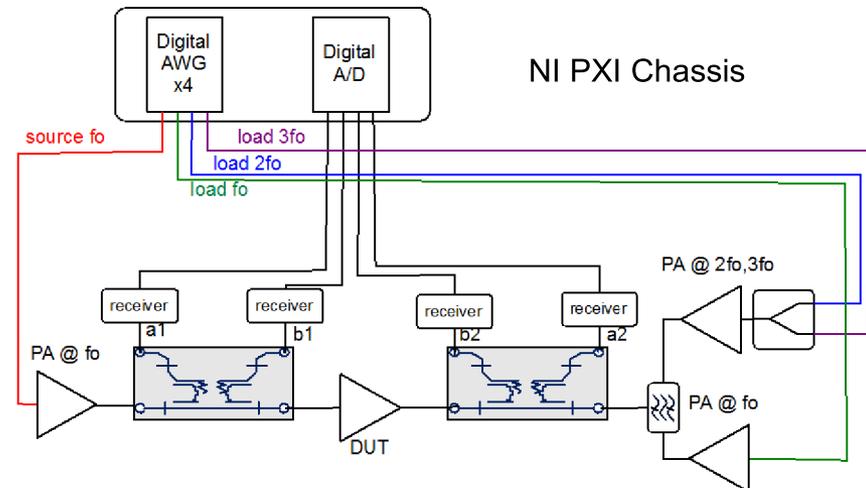
- Traditional passive Load-pull uses mechanical tuners to present reflection to device
- Active load-pull uses injection amplifiers to obtain Γ
 - closed loop uses signal from DUT
 - open loop uses synchronous AWG source
- Active open loop
 - complex modulated waveforms
 - harmonic control
 - high Γ





Open Loop Active Load-pull

- Mixed-Signal Active Load-pull (MSALPS) developed by Anteverta-mw and Maury Microwave
- 4 tuning loops – source f_0 , load f_0 , $2f_0$, and $3f_0$
- Measurement procedure:
 - samples a and b waves
 - iterates to achieve impedance
 - measures large signal performance

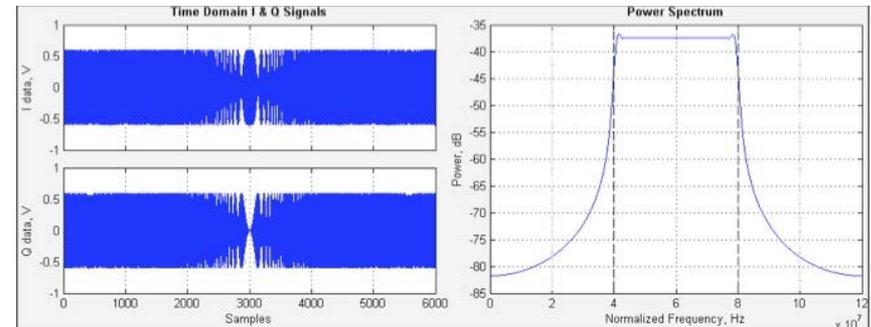
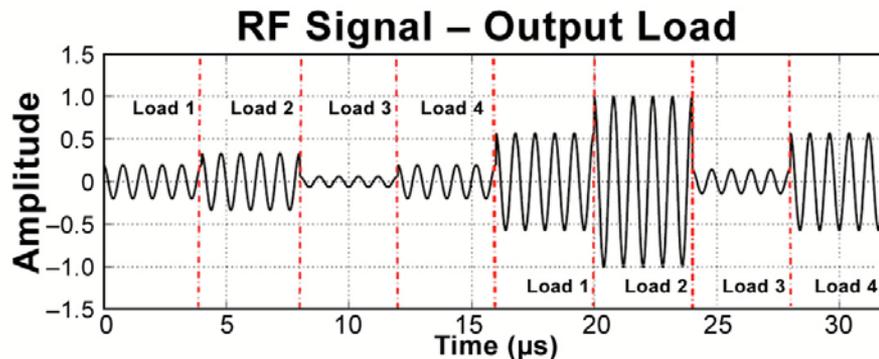




MSALPS capabilities

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- **Real-time mode allows rapid characterization of multiple impedances**
 - reduces characterization time (hours to minutes)
- **Load-pull modulated signals**
 - AWGs allow for inject single tone or complex signals
 - simulate pulsed chirp waveform response
 - perform frequency dependent load-pull
- **Phase reference**
 - calculate dynamic voltage and current
 - determine class of operation, peak currents and voltages, optimize waveform



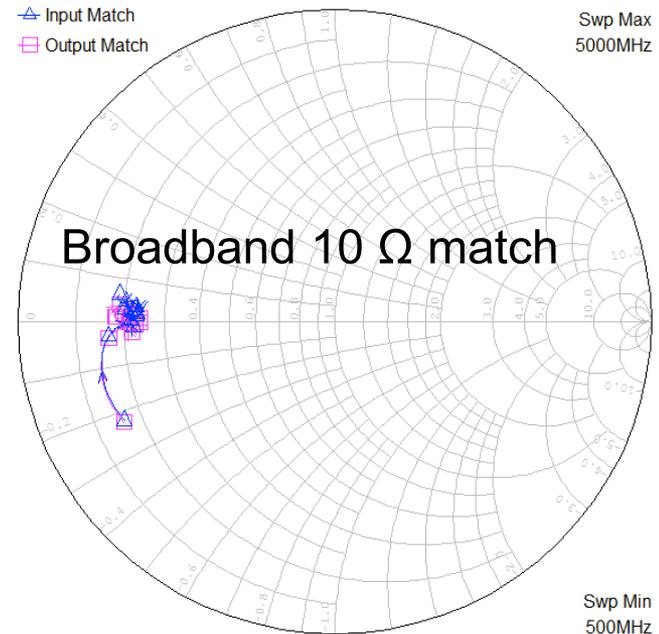
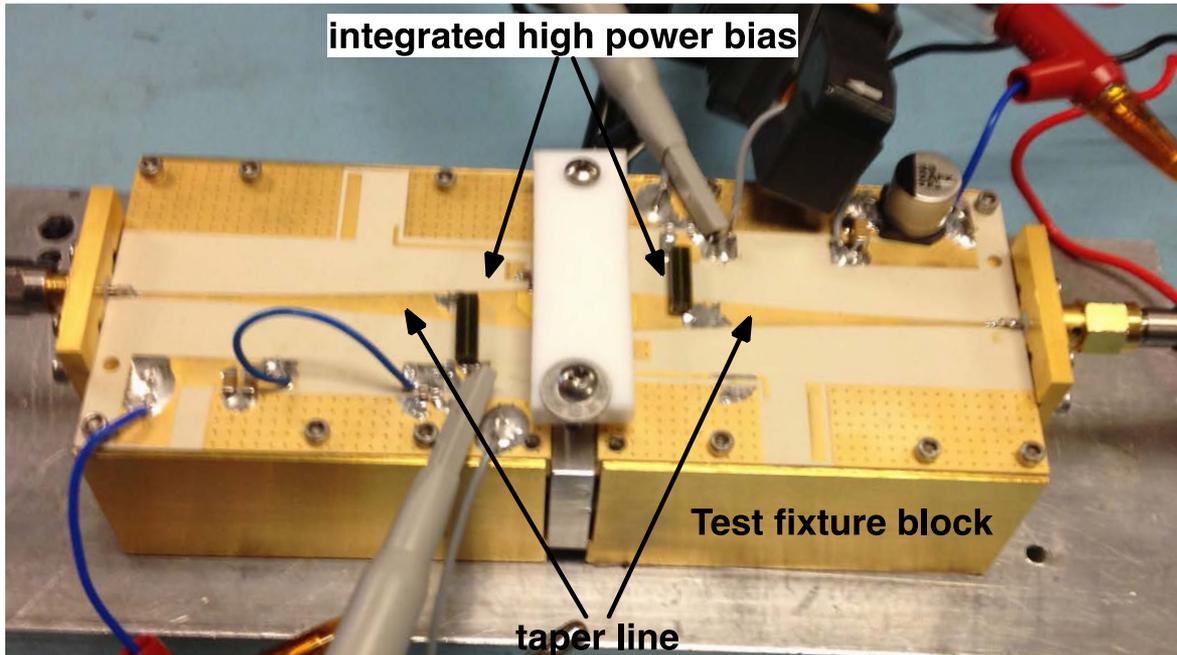


High-Power Test Fixture Design

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- **Active load-pull requires high-power injection amplifiers**
 - 120 W device with a 50 Ω system impedance → **700 W injection amp!**
 - 10 Ω transforming fixture ↓ **100 W injection amplifier**
- **Test fixture design requirements**
 - 50 Ω to 10 Ω transition - wide bandwidth
 - low-loss - integrated high-power bias

} **Klopfenstein taper**

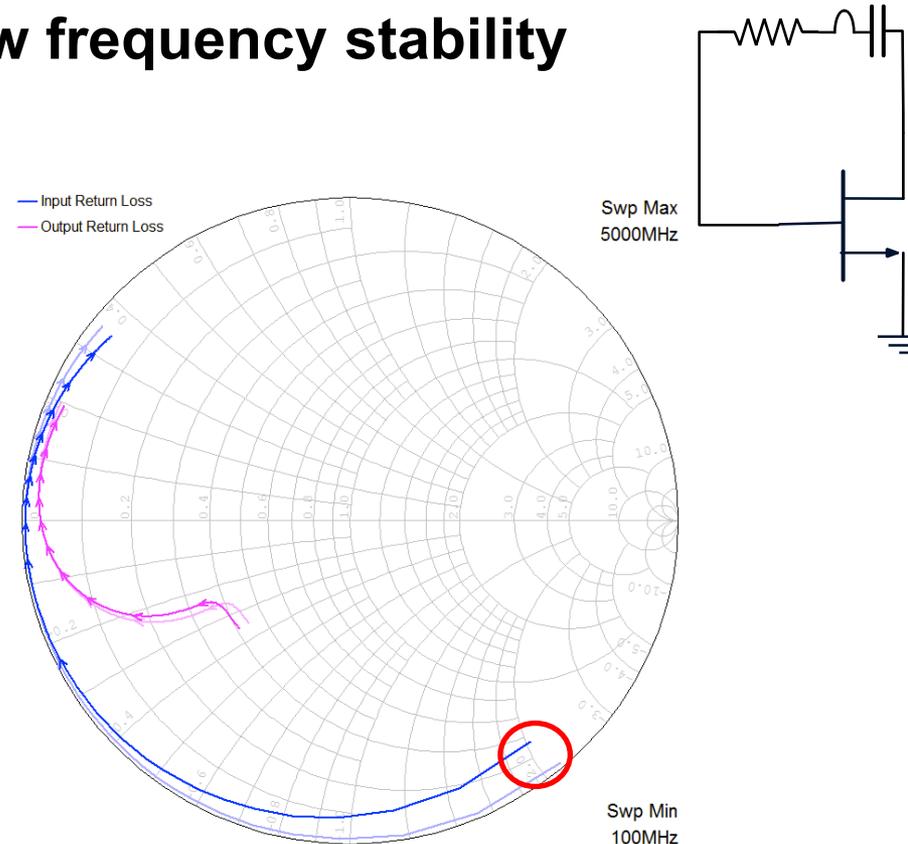
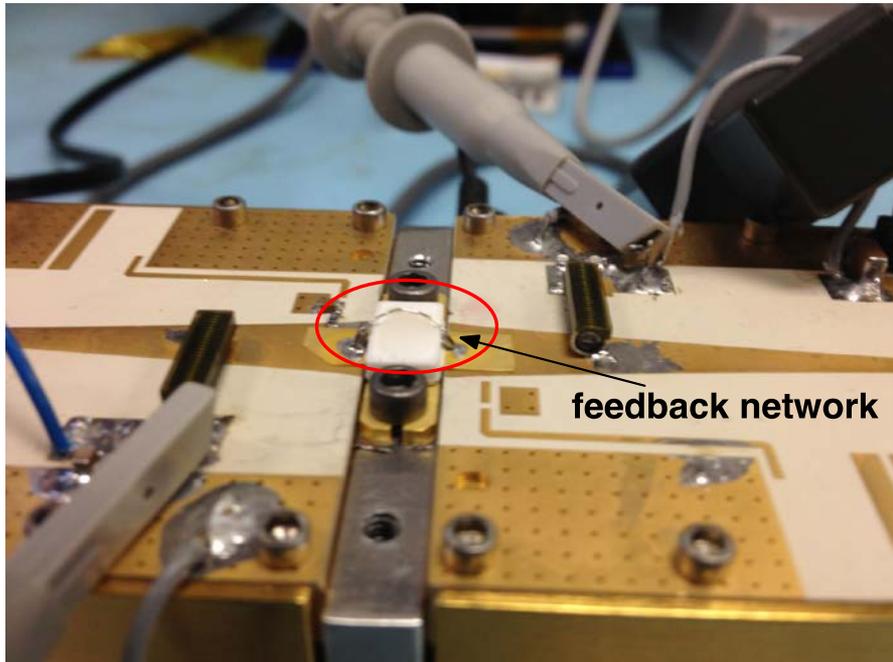




DUT Stability and Feedback

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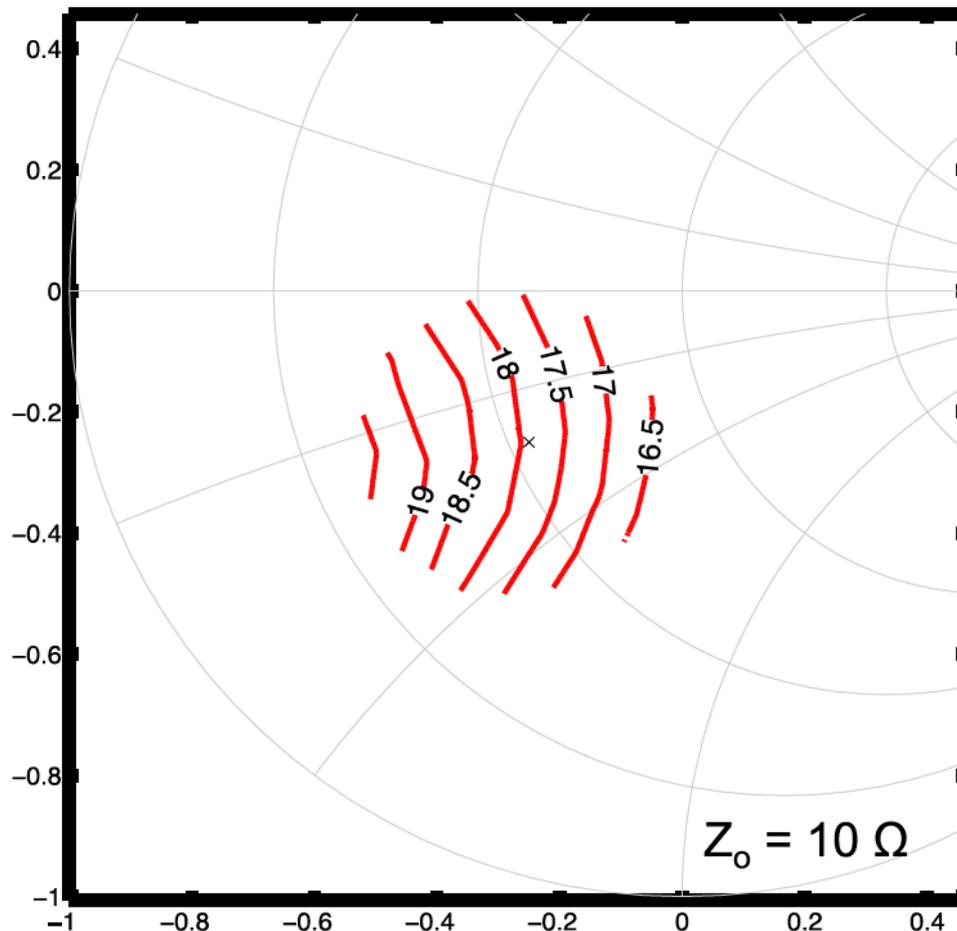
- **Device stability a concern for high power devices**
 - Large device → low impedance prone to oscillations
 - High-power could exceed thermal rating → catastrophic failures
- **Feedback network to improve low frequency stability**





Source match

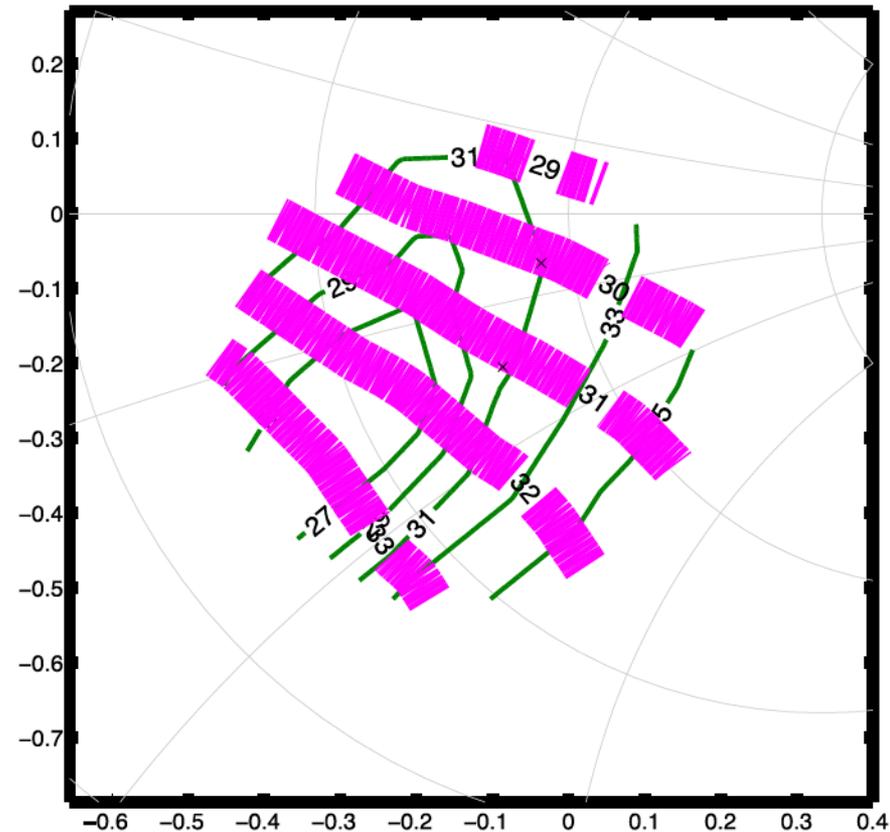
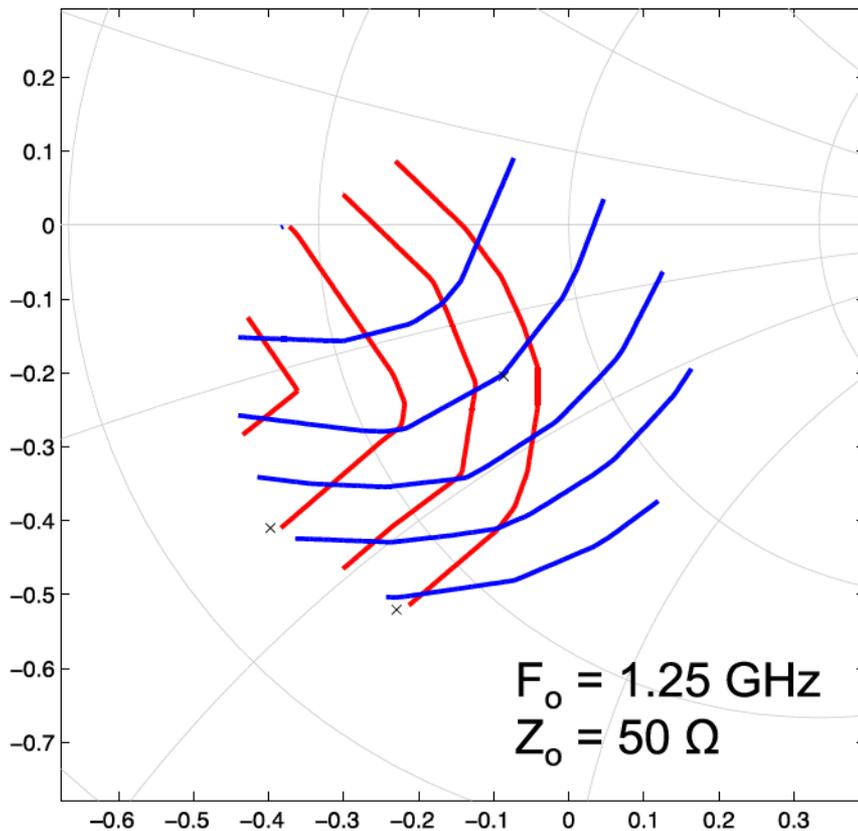
- GaN HEMTs → low input impedance
 - Trade-off between gain, stability, and bandwidth





Load tuning

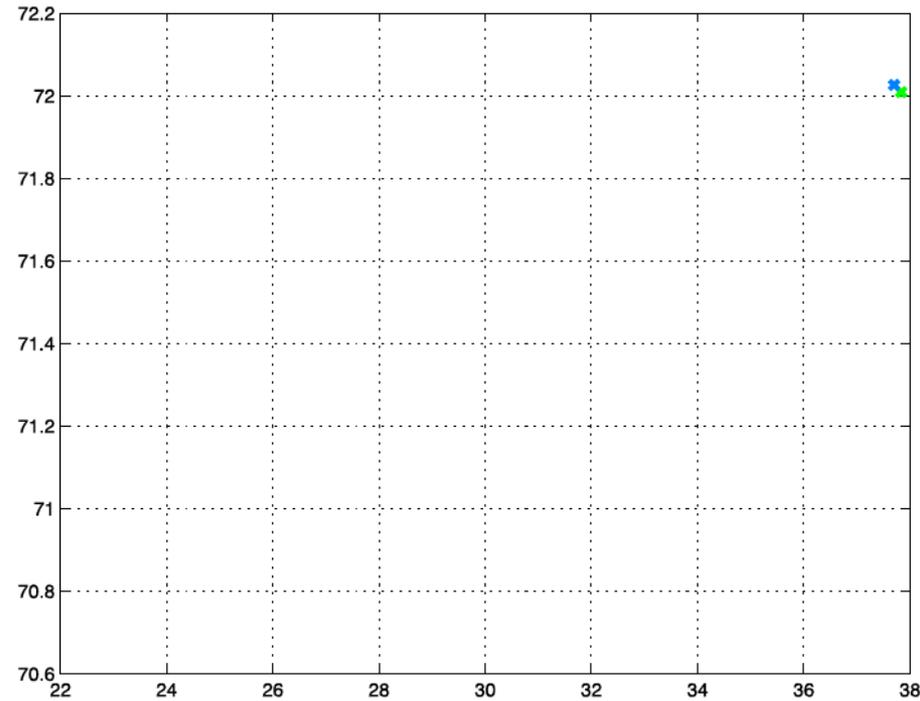
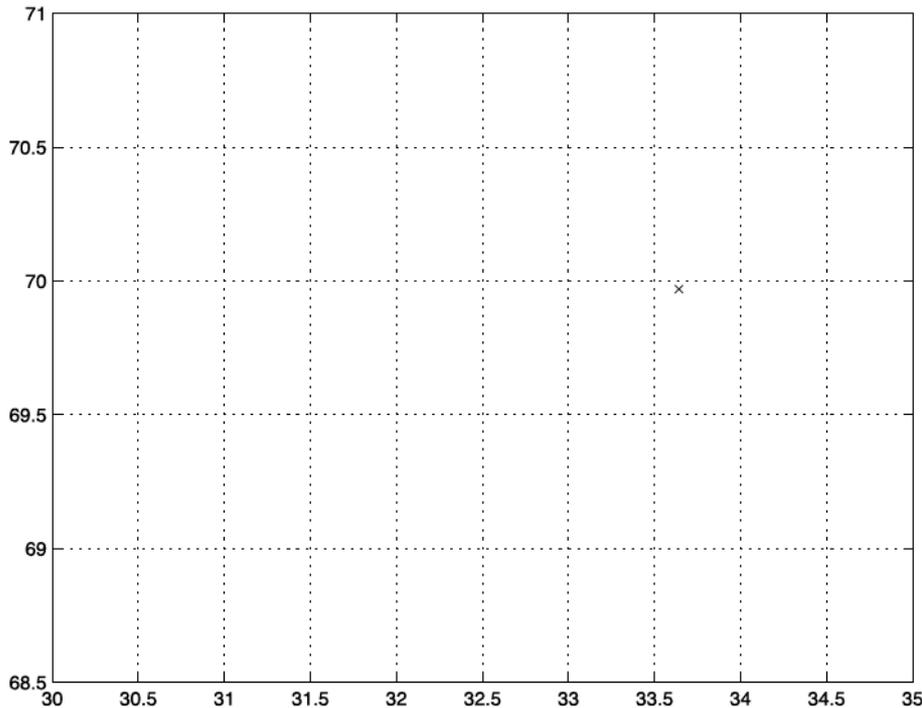
- Load-pull with no harmonic control
 - $P_{\text{out}} \sim 50 \text{ dBm}$
 - PAE > 50 %
 - Harmonic levels $\sim 30 \text{ dBm}$ ($\sim 20 \text{ dBc}$)





Harmonic tuning

- swept harmonic at $\Gamma = 0.8$ over all phase angles
 - optimal harmonic impedances will be reflective
 - harmonic levels reduced to below 30 dBc
 - PAE improved to over 70 %

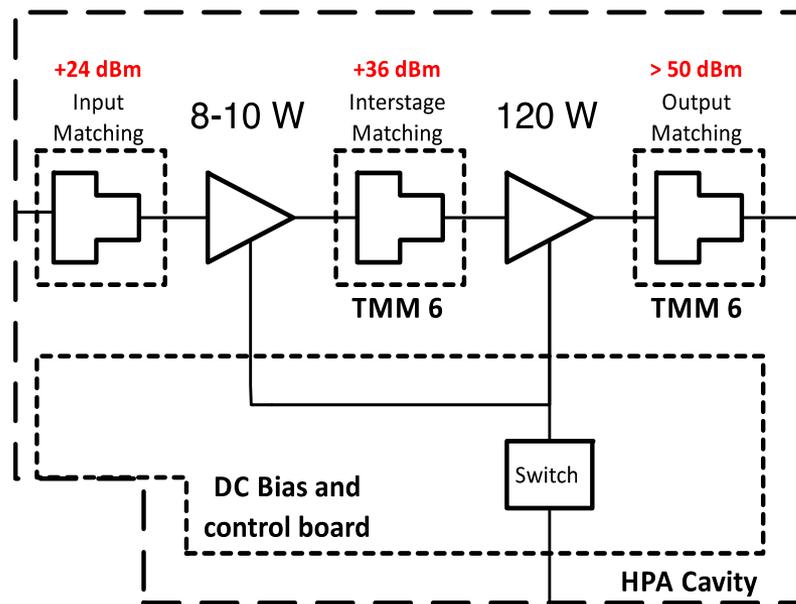




Proposed HPA Topology

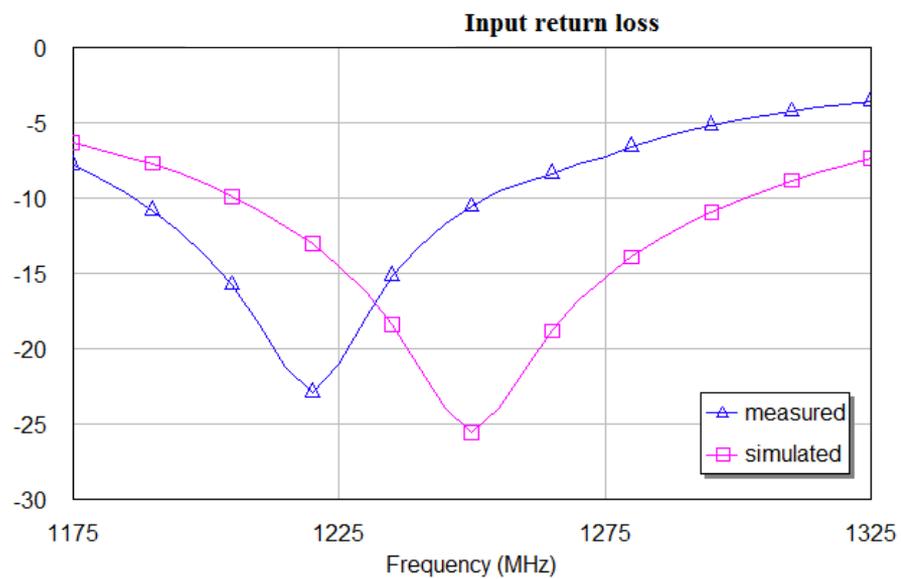
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- **Transitioned to new GaN HEMT vendor**
- **Two-stage HPA design**
 - 8-10 W GaN HEMT 1st stage
 - 120 W GaN HEMT 2nd stage
 - Input, interstage, and output matching networks on TMM 6
 - 10 Ω interstage matching
- **Separate DC bias / control board**
 - drain switching
 - gate dropout protection



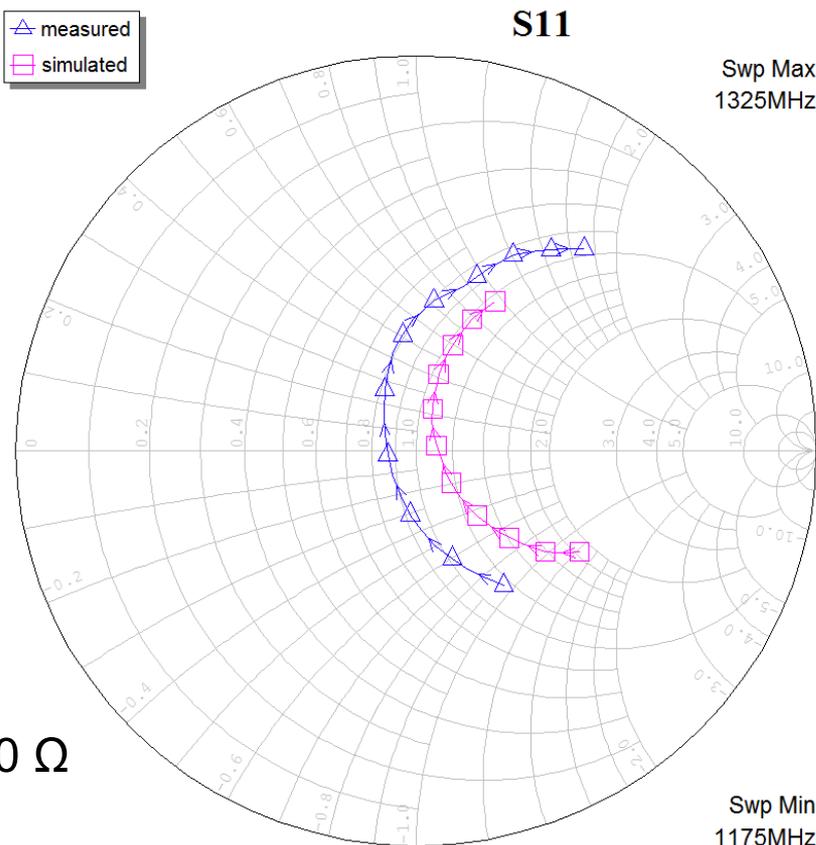


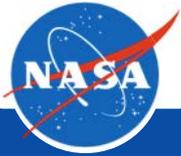
8W to 100W interstage match



△ measured
□ simulated

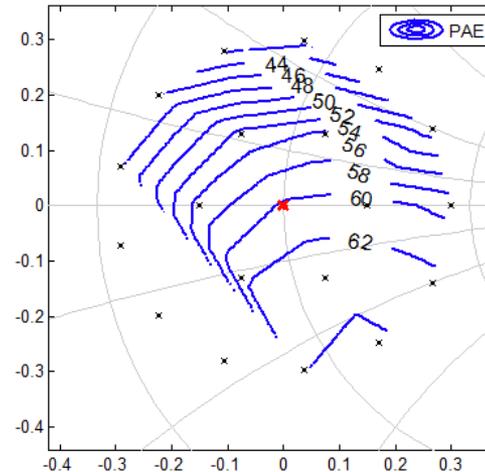
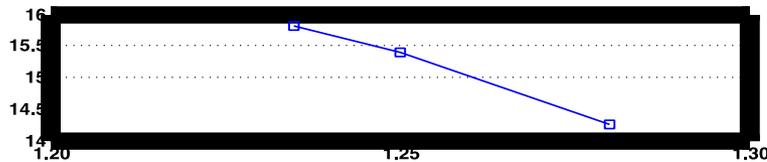
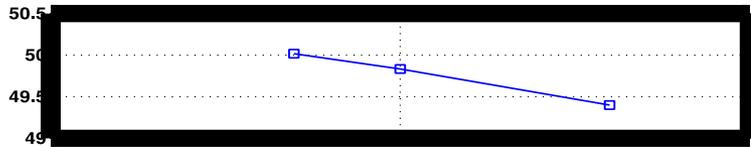
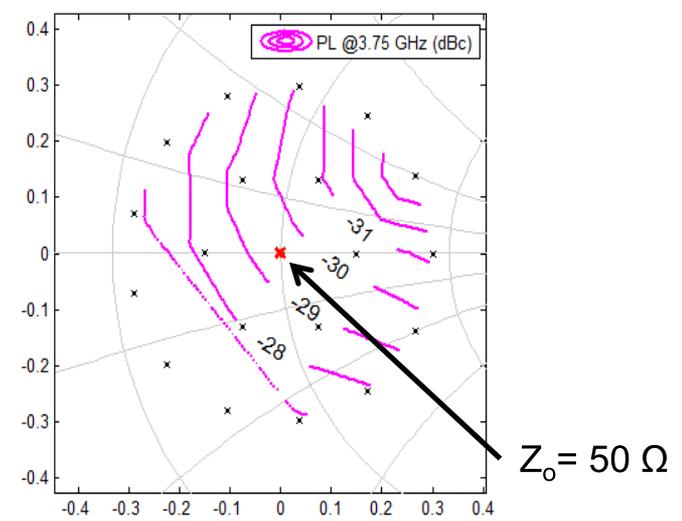
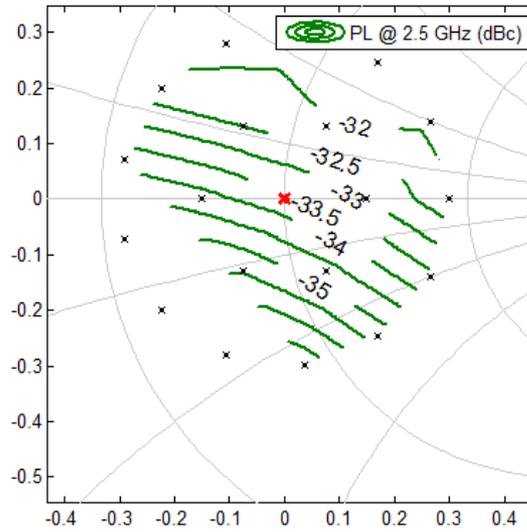
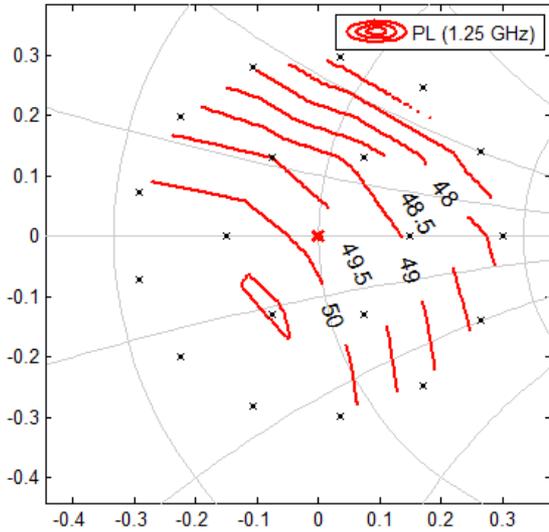
$Z_0 = 10 \Omega$





100 W Output match

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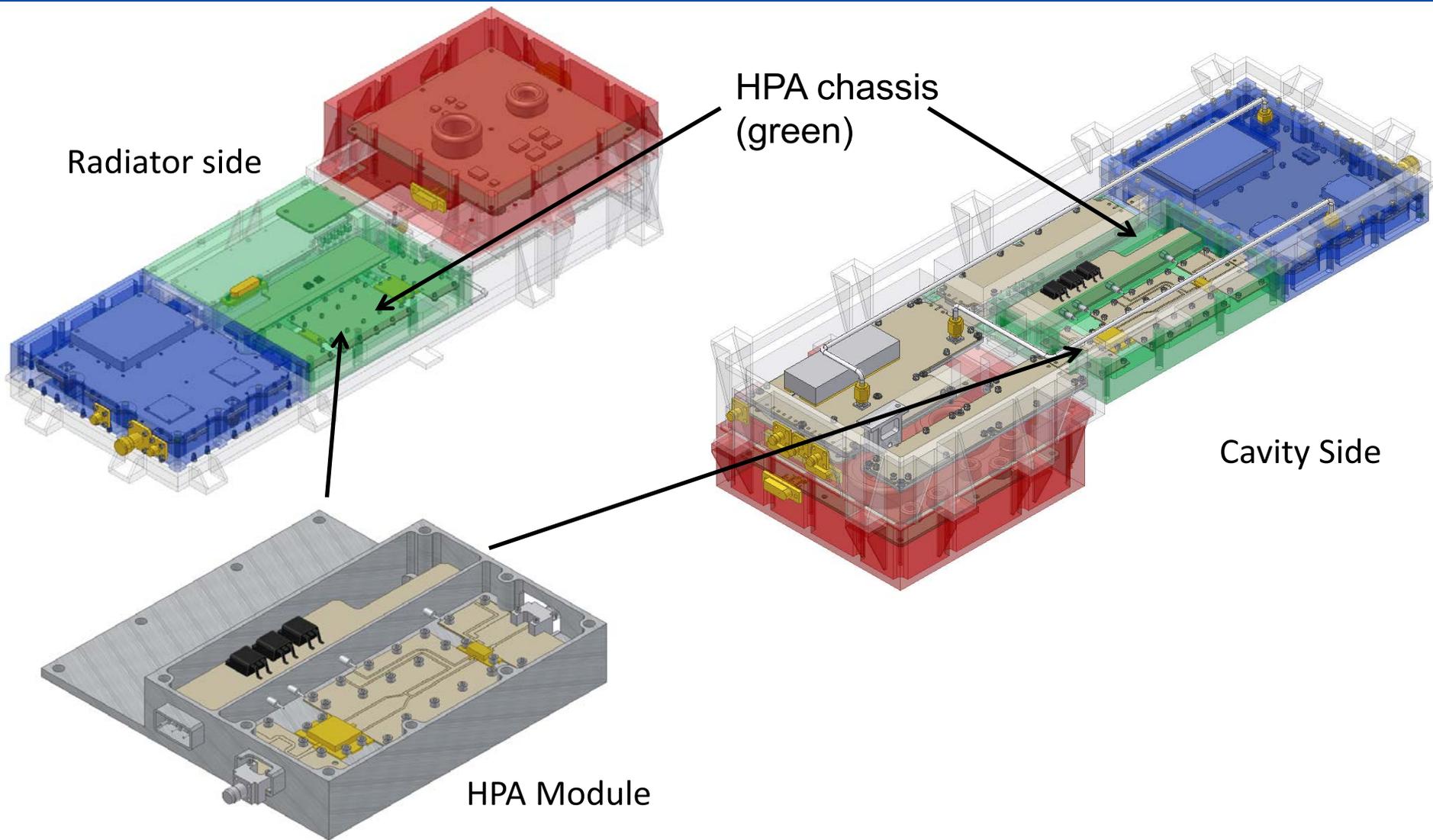


New part has slightly lower PAE



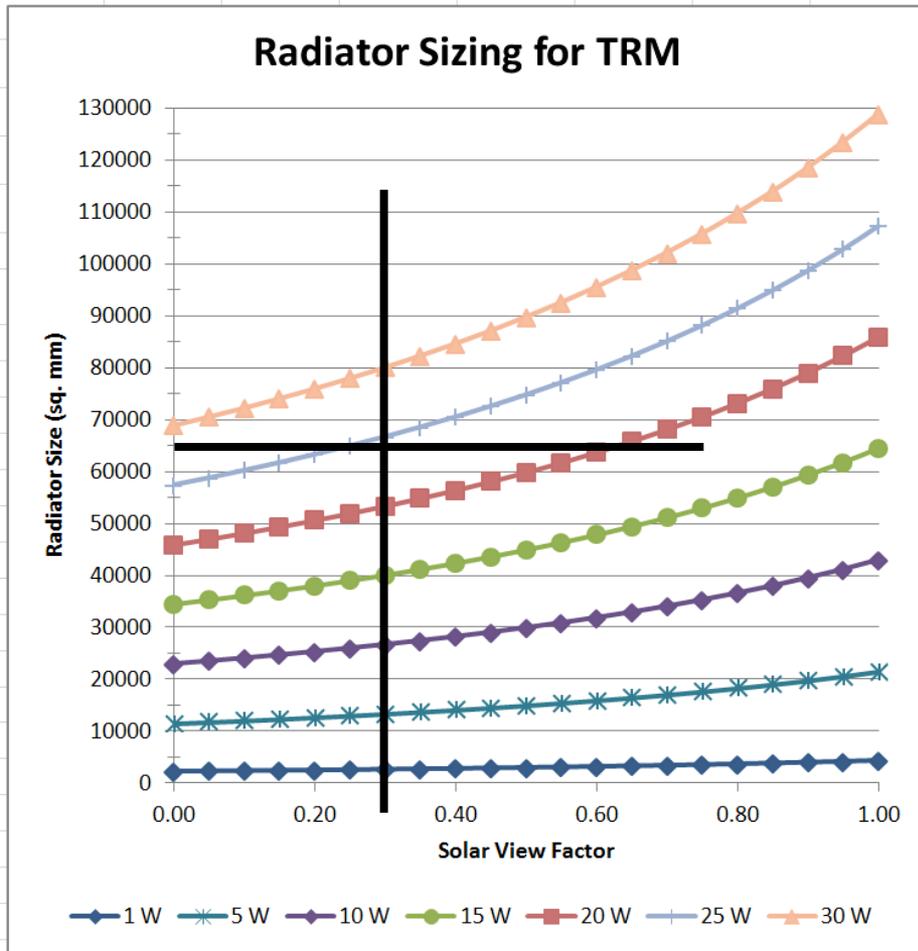
Overview TRM Configuration

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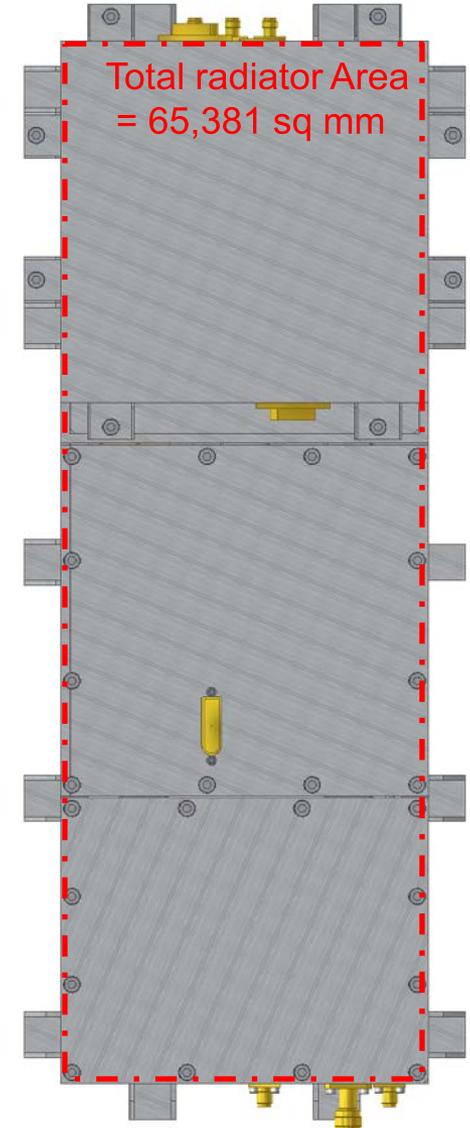




Thermal Design



Estimated Power Dissipation = 22W





Conclusions

- **SweepSAR requires high peak power, high-efficiency HPA**
 - GaN HEMT technology
 - Active Load-pull system for high-efficiency design
- **Complexities of Load-pulling high power part**
 - Test fixture design
 - Stability enhancement techniques
- **Load-pull results on 100 W GaN HEMT**
 - ~ 50 dBm output power
 - ~ 70 % PAE
 - Harmonic levels improved to below 30 dBc with harmonic tuning
- **Rev 1 HPA measured results**
 - ~ 50 dBm Pout
 - ~ 60 % PAE
 - 30 dBc harmonic levels